

# NTR5103N

## MOSFET – Single, N-Channel, Small Signal, SOT-23 60 V, 310 mA

### Features

- Low  $R_{DS(on)}$
- Small Footprint Surface Mount Package
- Trench Technology
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Low Side Load Switch
- Level Shift Circuits
- DC-DC Converter
- Portable Applications i.e. DSC, PDA, Cell Phone, etc.

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	60	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 30$	V
Drain Current (Note 1) Steady State	$I_D$	260 190	mA
$t < 5\text{ s}$		310 220	
Power Dissipation (Note 1) Steady State $t < 5\text{ s}$	$P_D$	300 420	mW
Pulsed Drain Current ( $t_p = 10\text{ }\mu\text{s}$ )	$I_{DM}$	1.2	A
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	300	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5\text{ s}$ (Note 1)	$R_{\theta JA}$	300	

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)

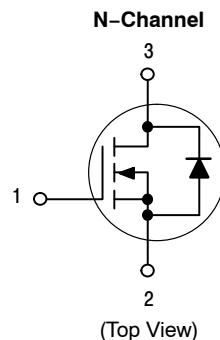


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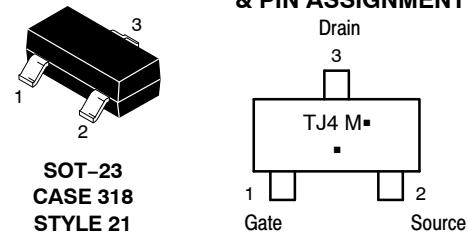
$V_{(\text{BR})DSS}$	$R_{DS(\text{on})}$ MAX	$I_D$ MAX (Note 1)
60 V	3.0 $\Omega$ @ 4.5 V	310 mA
	2.5 $\Omega$ @ 10 V	

### Simplified Schematic



(Top View)

### MARKING DIAGRAM & PIN ASSIGNMENT



TJ4 = Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTR5103NT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

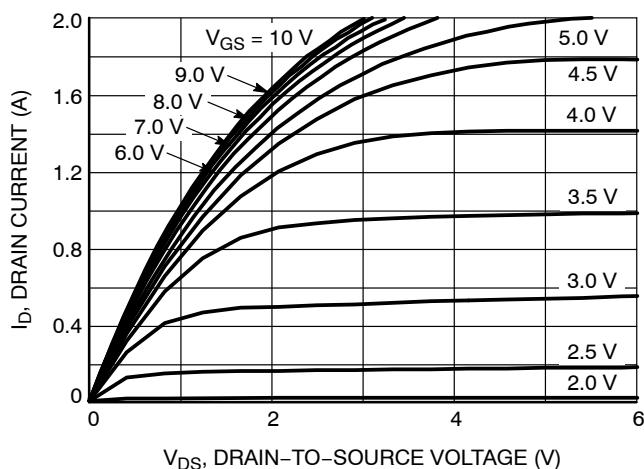
Parameter	Symbol	Test Condition		Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>							
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$		60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}/T_J}$				75		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}$ , $V_{\text{DS}} = 60 \text{ V}$	$T_J = 25^\circ\text{C}$		1		$\mu\text{A}$
			$T_J = 125^\circ\text{C}$			500	
Gate-to-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{DS}} = 0 \text{ V}$ , $V_{\text{GS}} = \pm 30 \text{ V}$			200		nA
<b>ON CHARACTERISTICS (Note 2)</b>							
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}$ , $I_D = 250 \mu\text{A}$		1.9		2.6	V
Negative Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})/T_J}$				4.4		$\text{mV}/^\circ\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}$ , $I_D = 240 \text{ mA}$			1.0	2.5	$\Omega$
		$V_{\text{GS}} = 4.5 \text{ V}$ , $I_D = 50 \text{ mA}$			1.4	3.0	
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}} = 5 \text{ V}$ , $I_D = 200 \text{ mA}$			530		mS
<b>CHARGES AND CAPACITANCES</b>							
Input Capacitance	$C_{\text{ISS}}$	$V_{\text{GS}} = 0 \text{ V}$ , $f = 1 \text{ MHz}$ , $V_{\text{DS}} = 25 \text{ V}$		26.7	40	pF	
Output Capacitance	$C_{\text{OSS}}$			4.6			
Reverse Transfer Capacitance	$C_{\text{RSS}}$			2.9			
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 5 \text{ V}$ , $V_{\text{DS}} = 10 \text{ V}$ , $I_D = 240 \text{ mA}$		0.81		nC	
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$			0.31			
Gate-to-Source Charge	$Q_{\text{GS}}$			0.48			
Gate-to-Drain Charge	$Q_{\text{GD}}$			0.08			
<b>SWITCHING CHARACTERISTICS, <math>V_{\text{GS}} = V</math> (Note 3)</b>							
Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 10 \text{ V}$ , $V_{\text{DD}} = 30 \text{ V}$ , $I_D = 200 \text{ mA}$ , $R_{\text{G}} = 10 \Omega$		1.7		ns	
Rise Time	$t_r$			1.2			
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			4.8			
Fall Time	$t_f$			3.6			
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>							
Forward Diode Voltage	$V_{\text{SD}}$	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = 200 \text{ mA}$	$T_J = 25^\circ\text{C}$		0.79	1.2	V
			$T_J = 85^\circ\text{C}$		0.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

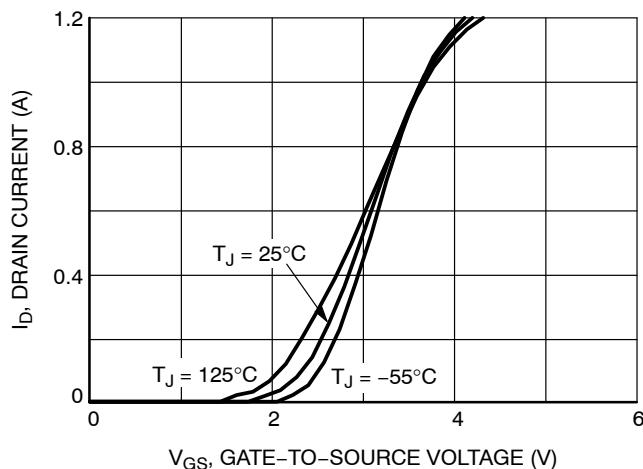
2. Pulse Test: pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$

3. Switching characteristics are independent of operating junction temperatures

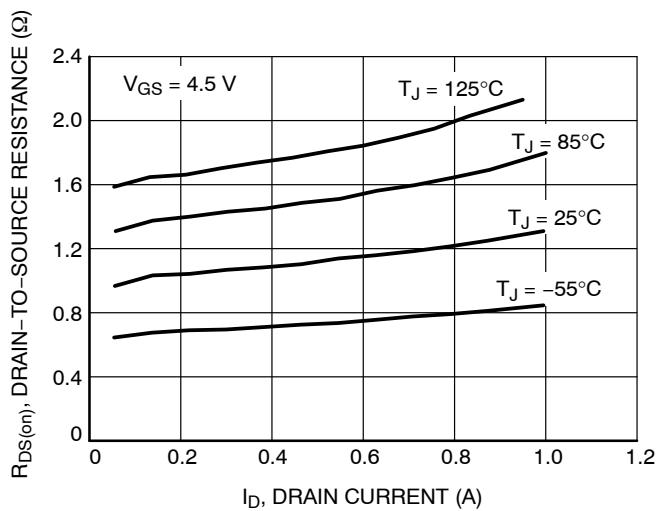
**TYPICAL CHARACTERISTICS**



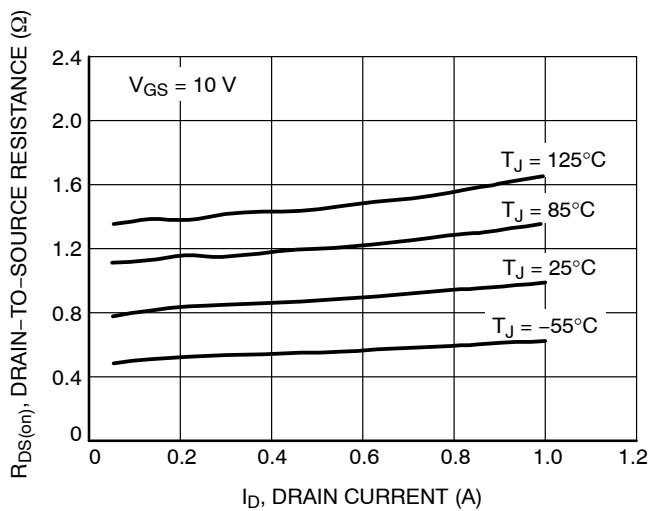
**Figure 1. On-Region Characteristics**



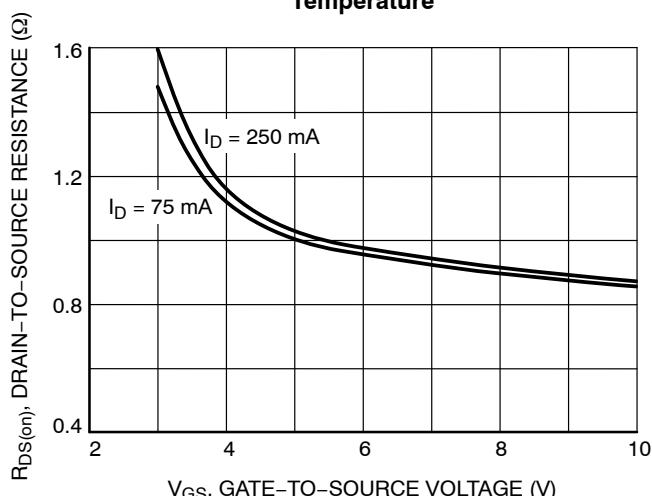
**Figure 2. Transfer Characteristics**



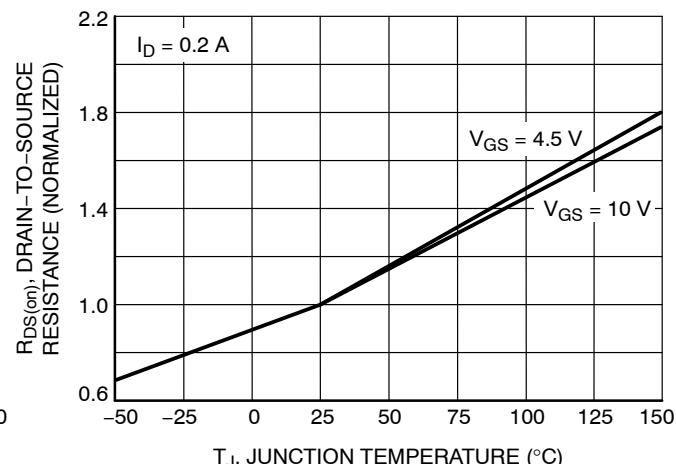
**Figure 3. On-Resistance vs. Drain Current and Temperature**



**Figure 4. On-Resistance vs. Drain Current and Temperature**

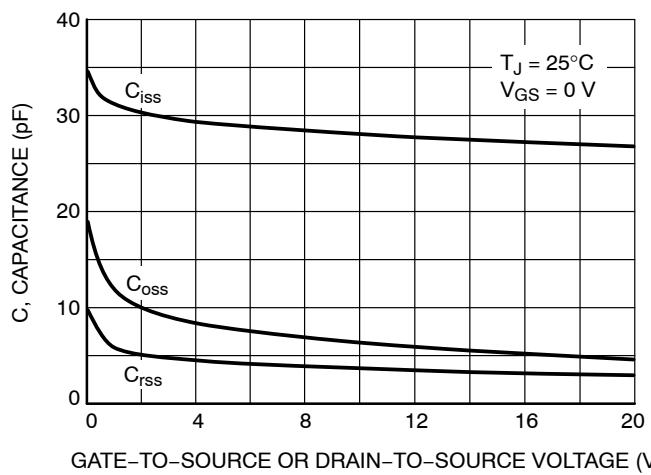


**Figure 5. On-Resistance vs. Gate-to-Source Voltage**

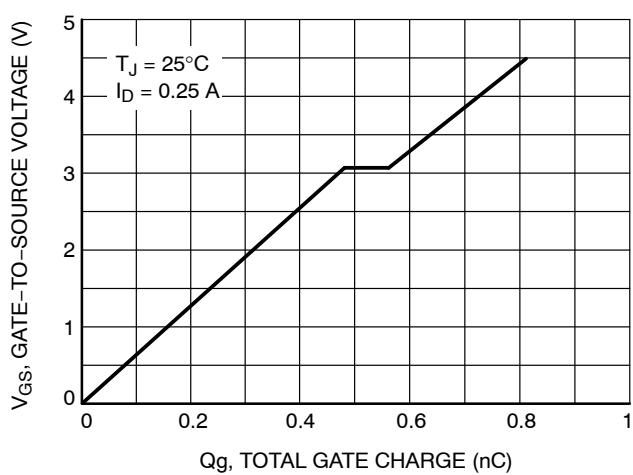


**Figure 6. On-Resistance Variation with Temperature**

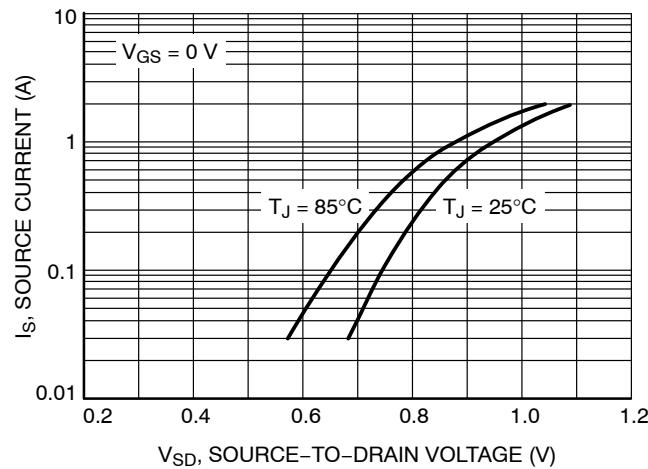
**TYPICAL CHARACTERISTICS**



**Figure 7. Capacitance Variation**

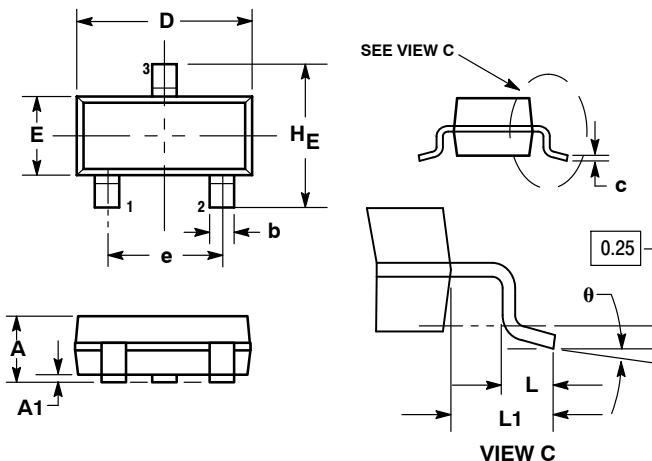


**Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge**



**Figure 9. Diode Forward Voltage vs. Current**

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AP

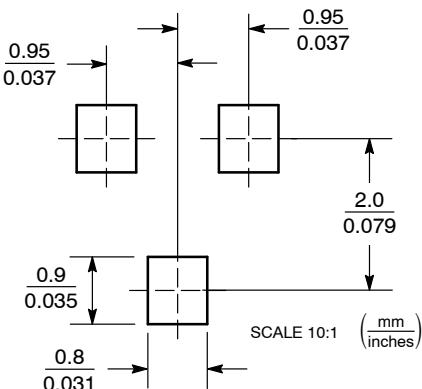
## NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

## SOLDERING FOOTPRINT



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